

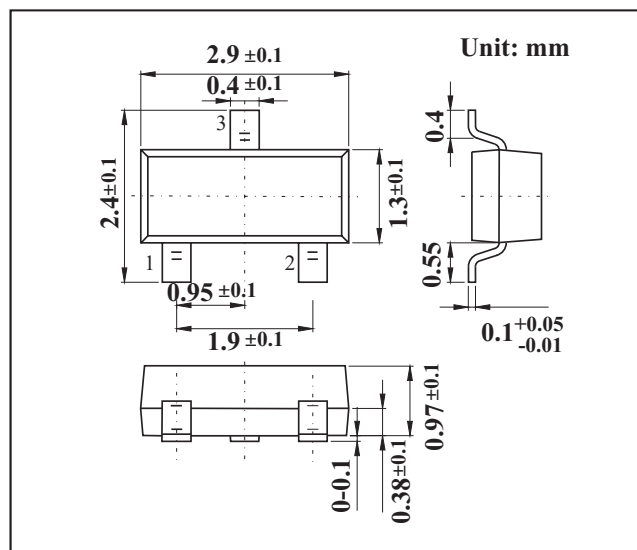
SOT-23 Plastic-Encapsulate Transistors

FEATURES

- Low Cob.Cob=2.0pF (Typ.)
- NPN Transistors

MECHANICAL DATA

- Case style:SOT-23molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	60	V
Collector-emitter voltage	V _{CEO}	50	V
Emitter-base voltage	V _{EBO}	7	V
Collector current	I _C	0.15	A
Collector power dissipation	P _C	0.2	W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	- 5 5 t o + 1 5 0	°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CBO}	I _C = 50 μA, I _E = 0	60			V
Collector- emitter breakdown voltage	V _{CEO}	I _C = 1 mA, I _B = 0	50			
Emitter - base breakdown voltage	V _{EBO}	I _E = 50 μ A, I _C = 0	7			
Collector-base cut-off current	I _{CBO}	V _{CB} = 60 V , I _E = 0			100	nA
Emitter cut-off current	I _{EBO}	V _{EB} = 7V , I _C =0			100	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =50 mA, I _B =5mA			0.4	V
Base - emitter saturation voltage	V _{BE(sat)}	I _C =50 mA, I _B =5mA			1.2	
DC current gain	h _{FE}	V _{CE} = 6V, I _C = 1mA	120		560	
Collector output capacitance	C _{ob}	V _{CB} = 12V, I _E = 0,f=1MHz		2	3.5	pF
Transition frequency	f _T	V _{CE} = 12V, I _E = -2mA,f=100MHz	80			MHz

RATINGS AND CHARACTERISTIC CURVES

